

STTH8S06

Turbo 2 ultrafast high voltage rectifier

Features

- Ultrafast recovery
- Low reverse recovery current
- Reduces losses in diode and switching transistor
- Low thermal resistance
- Higher frequency operation
- Insulated TO-220FPAC version
 - Insulation voltage = 1500 V rms
 - Package capacitance = 12 pF

Description

ST's **STTH8S06** is a state of the art ultrafast recovery diode. By the use of **600 V Pt doping planar technology**, this diode will out-perform the power factor corrections circuits operating in hardswitching conditions. The extremely low reverse recovery current of the **STTH8S06**, reduces significantly the switching power losses of the MOSFET and thus increases the efficiency of the application. This leads designers to reduce the size of their heatsinks.

This device is also intended for applications in power supplies and power conversions systems, motor drive, and other power switching applications.

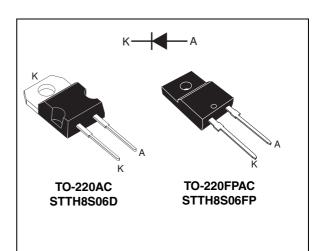


Table 1.Device summary

I _{F(AV)}	8 A
V _{RRM}	600 V
I _{RM} (typ.)	4.4 A
T _j (max)	175 °C
V _F (typ)	1.5 V
t _{rr} (typ)	12 ns

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Characteristics

1 Characteristics

Table 2. Absolute ratings (limiting values)

Symbol	Param	Value	Unit	
V _{RRM}	Repetitive peak reverse voltage	600	V	
I _{F(AV)}	Average forward current	8	А	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms	60	А
T _{stg}	Storage temperature range	-65 to + 175	°C	
Тj	Maximum operating junction temperature		175	°C

Table 3. Thermal parameter

Symbol	Parameter	Maximum	Unit	
В	lunction to enco	TO-220AC	3.0	°C/W
R _{th(j-c)}	Junction to case	TO220FPAC	5.5	C/ VV

Table 4. Static electrical characteristics

Symbol	Parameter	Test co	Min.	Тур	Max.	Unit	
		T _j = 25 °C	V - 600 V			20	
'R	I _R Reverse leakage current	T _j = 125 °C	V _R = 600 V		25	200	μA
V Eenword voltage drop		T _j = 25 °C	9 A			3.4	V
V _F I	Forward voltage drop	T _j = 125 °C	I _F = 8 A		1.5	1.9	v

To evaluate the maximum conduction losses use the following equation: P = 1.20 x $I_{F(AV)}$ + 0.087 ${I_F}^2_{(RMS)}$

Table 5. Dynamic electrical characteristics

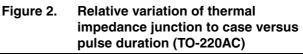
Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
t _{rr}	Reverse recovery time	$I_F = 1 \text{ A}, dI_F/dt = -200 \text{ A}/\mu \text{s}, V_R = 30 \text{ V}$			12	18	ns
I _{RM}	Reverse current				1.6	2.2	А
S _{factor}	Softness factor	T _j = 25 °C	$I_F = 8 \text{ A, } dI_F/dt = -200 \text{ A/}\mu\text{s},$ $V_R = 200 \text{ V}$		1		-
Q _{rr}	Reverse recovery charges				17		nC
I _{RM}	Reverse current				4.4	6.0	А
S _{factor}	Softness factor	T _j = 125 °C	C $ I_F = 8 \text{ A}, dI_F/dt = -200 \text{ A}/\mu\text{s}, V_R = 200 \text{ V}$		0.3		-
Q _{rr}	Reverse recovery charges		11		90		nC



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STTH8S06

Figure 1. Forward voltage drop versus forward current



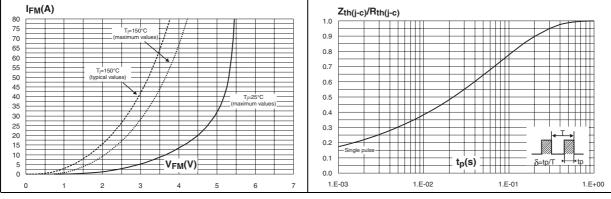
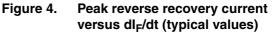
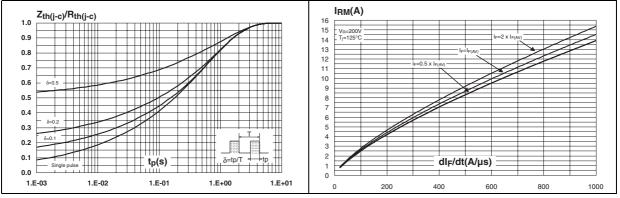


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration(TO-220FPAC)

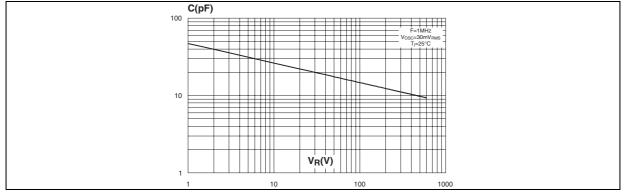




Characteristics

Figure 5. Reverse recovery time versus dl_F/dt Figure 6. **Reverse recovery charges versus** (typical values) dl_F/dt (typical values) t_{rr}(ns) Q_{rr}(nC) – I_F=2 x I V_R=200V T_j=125°C V_R=200V T_j=125°C IF=IF(A 2 x I= F=0.5 =0.5 x I_{F(A)} dl_F/dt(A/µs) dl_F/dt(A/µs)







- 2 Package information
 - Epoxy meets UL94, V0
 - Cooling method: by conduction (C)
 - Recommended torque value: 0.4 to 0.6 N·m

In order to meet environmental requirements, ST (also) offers these devices in ECOPACK® packages. ECOPACK® packages are Lead-free. The category of second level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label.

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			Dimer	nsions	
	Ref.	Millin	neters	Inches	
		Min.	Max.	Min.	Max.
	Α	4.40	4.60	0.173	0.181
H2 A	С	1.23	1.32	0.048	0.051
	D	2.40	2.72	0.094	0.107
	Е	0.49	0.70	0.019	0.027
	F	0.61	0.88	0.024	0.034
	F1	1.14	1.70	0.044	0.066
	G	4.95	5.15	0.194	0.202
	H2	10.00	10.40	0.393	0.409
	L2	16.40 typ.		0.645 typ.	
E L4	L4	13.00	14.00	0.511	0.551
	L5	2.65	2.95	0.104	0.116
	L6	15.25	15.75	0.600	0.620
G	L7	6.20	6.60	0.244	0.259
	L9	3.50	3.93	0.137	0.154
	М	2.6	typ.	0.102	2 typ.
	Diam. I	3.75	3.85	0.147	0.151

Table 6. TO-220AC dimensions

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			Dimer	nsions	
	Ref.	Millim	neters	Inches	
		Min.	Max.	Min.	Max.
	А	4.4	4.6	0.173	0.181
H A	В	2.5	2.7	0.098	0.106
	D	2.5	2.75	0.098	0.108
Dia	Е	0.45	0.70	0.018	0.027
	F	0.75	1	0.030	0.039
	F1	1.15	1.70	0.045	0.067
L2 L7 L7	G	4.95	5.20	0.195	0.205
	G1	2.4	2.7	0.094	0.106
	Н	10	10.4	0.393	0.409
L4	L2	16	Тур.	0.63	Тур.
	L3	28.6	30.6	1.126	1.205
	L4	9.8	10.6	0.386	0.417
G	L5	2.9	3.6	0.114	0.142
	L6	15.9	16.4	0.626	0.646
	L7	9.00	9.30	0.354	0.366
	Dia.	3.00	3.20	0.118	0.126

Table 7. TO-220FPAC dimensions



3 Ordering information

Table 8.Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH8S06D	STTH8S06D	TO-220AC	1.9 g	50	Tube
STTH8S06FP	STTH8S06FP	TO-220FPAC	1.64 g	50	Tube

4 Revision history

Table 9.Document revision history

Date	Revision	Description of changes
18-Dec-2007	1	First issue.

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